

# SILICON NPN TRANSISTOR EPITAXIAL PLANAR TYPE (PCT PROCESS)

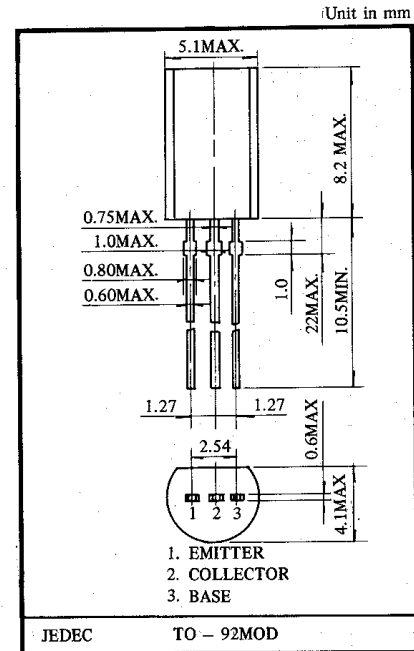
# KTC 1627A

## APPLICATIONS

- Driver Stage Amplifier Applications.
- Voltage Amplifier Applications.

## FEATURES

- Complementary to KTA817A
- Driver Stage Application of 30 to 35 Watts Amplifiers.



## MAXIMUM RATINGS (Ta=25 °C)

CHARACTERISTIC	SYMBOL	RATING	UNIT	CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V <sub>CBO</sub>	80	V	Emitter Current	I <sub>E</sub>	-400	mA
Collector-Emitter Voltage	V <sub>CEO</sub>	80	V	Collector Dissipation	P <sub>C</sub>	800	mW
Emitter-Base Voltage	V <sub>EBO</sub>	5	V	Junction Temperature	T <sub>j</sub>	150	°C
Collector Current	I <sub>C</sub>	400	mA	Storage Temperature	T <sub>stg</sub>	-55~150	°C

## ELECTRICAL CHARACTERISTICS (Ta=25 °C)

CHARACTERISTIC	SYMBOL	CONDITION	MIN.	TYP.	MAX	UNIT
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> =50V, I <sub>E</sub> =0	-	-	100	nA
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> =5V, I <sub>C</sub> =0	-	-	100	nA
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =5mA	80	-	-	V
DC Current Gain	h <sub>FE(1)</sub>	V <sub>CE</sub> =2V, I <sub>C</sub> =50mA	70	-	240	
	h <sub>FE(2)</sub>	V <sub>CE</sub> =2V, I <sub>C</sub> =200mA	40	-	-	
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =200mA, I <sub>B</sub> =20mA	-	-	0.4	V
Base-Emitter Voltage	V <sub>BE</sub>	V <sub>CE</sub> =2V, I <sub>C</sub> =5mA	0.55	-	0.8	V
Transition Frequency	f <sub>T</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =10mA	-	100	-	MHz
Collector Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V, f=1MHz	-	10	-	pF

NOTE: According to h<sub>FE</sub>(1), Classified as follows.

0	70-140	Y	120-240
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